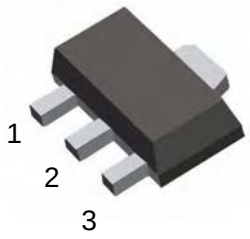
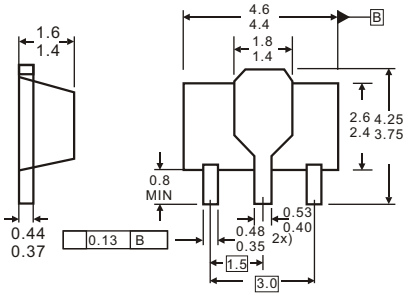
2SA1740

SOT-89 Transistor(PNP)



1. BASE
2. COLLECTOR
3. EMITTER

SOT-89



Dimensions in inches and (millimeters)

Features

- ✧ High breadown voltage
- ✧ Excellent h_{FE} linearlity

Marking: AK

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-400	V
V_{CEO}	Collector-Emitter Voltage	-400	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-200	mA
P_C	Collector Dissipation	500	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10μA,I_E=0	-400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-300V,I_E=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-100	nA
DC current gain	h_{FE}	V_{CE}=-10V,I_C=-50mA	60		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-50mA,I_B=-5mA			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-50mA,I_B=-5mA			-1	V
Transition frequency	f_T	V_{CE}=-30V,I_C=-10mA		70		MHz
Collector output capacitance	C_{ob}	V_{CB}=-30V,I_E=0,f=1MHz		5		pF
Turn-ON Time	t_{on}	V_{CC}=-150V,I_c=-50mA, I_{B1}=-I_{B2}=-5mA		0.25		μs
Turn-OFF Time	t_{off}			5		μs

CLASSIFICATION OF h_{FE}

Rank	D	E
Range	60-120	100-200

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Typical Characteristics